

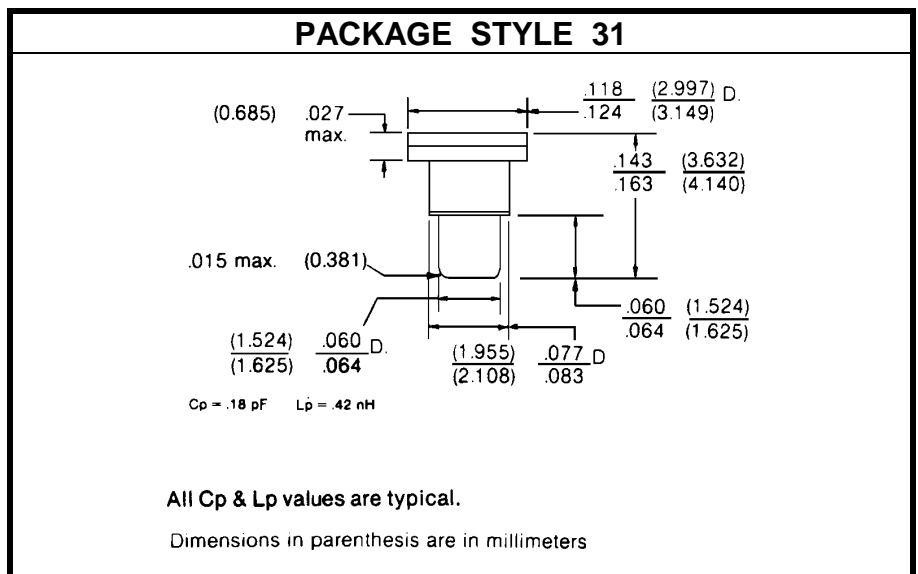
SILICON ABRUPT TUNING VARACTOR DIODE

DESCRIPTION:

The **ASI MV1863D** is a Passivated Epitaxial Silicon Abrupt Tuning Varactor Diode.

MAXIMUM RATINGS

I	100 mA
V	60 V
P_{DISS}	500 mW @ T _C = 25 °C
T_J	-65 °C to +175 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.3 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V _B	I _R = 10 μA	60			V
I _R	V _R = 55 V			100	μA
C _T	V _R = 4.0 V f = 1.0 MHz	4.23	4.70	5.17	pF
T _R	C = -4/C = -60 f = 1.0 MHz	2.6		3.3	RATIO
R _S	V _R = 4.0 V f = 500 MHz			1.1	Ohms
Q	V _R = 4.0 V f = 100 MHz	300			---
C _p	f = 1.0 MHz		0.18		pF
L _s			0.8		μH